

μ PA2737GR

P-channel MOSFET

 $-30 \text{ V}, -11 \text{ A}, 13 \text{ m}\Omega$

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Description

The μ PA2737GR is P-channel MOS Field Effect Transistor designed for DC/DC converter and power management applications of portable equipment.

Features

- $V_{DSS} = -30 \text{ V } (T_A = 25^{\circ}\text{C})$
- Low on-state resistance
 - --- R_{DS(on)} = 13 mΩ MAX. (V_{GS} = -10 V, I_D = -11 A)
- 4.5 V Gate-drive available
- Small and surface mount package (SOP-8)
- Pb-free and Halogen free



SOP-8

Ordering Information

Part No.	LEAD PLATING	PACKING	Package
μ PA2737GR-E1-AX	Ni / Pd / Au	Tono 2500 n/rool	SOP-8
μ PA2737GR-E2-AX	INI / Pu / Au	Tape 2500 p/reel	0.085 g TYP.

Absolute Maximum Ratings $(T_A = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to Source Voltage (V _{GS} = 0 V)	V _{DSS}	-30	V
Gate to Source Voltage (V _{DS} = 0 V)	V _{GSS}	∓20	V
Drain Current (DC)	I _{D(DC)}	∓11	Α
Drain Current (pulse) *1	I _{D(pulse)}	∓110	Α
Total Power Dissipation *2	P _{T1}	1.1	W
Total Power Dissipation (PW = 10 sec) *2	P _{T2}	2.5	W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{stg}	−55 to +150	°C
Single Avalanche Current *3	I _{AS}	11	Α
Single Avalanche Energy *3	E _{AS}	12.1	mJ

Thermal Resistance

Channel to Ambient Thermal Resistance *2 R_{th(ch-A)} 114 °C/W

Notes: *1. PW \leq 10 μ s, Duty Cycle \leq 1%

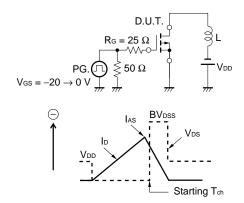
- *2. Mounted on a glass epoxy board of 25.4 mm x 25.4 mm x 0.8 mmt
- *3. Starting $T_{ch} = 25$ °C, $V_{DD} = -15$ V, $R_G = 25$ Ω , $V_{GS} = -20 \rightarrow 0$ V, L = 100 μH

Electrical Characteristics (T_A = 25°C)

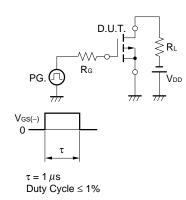
Item	Symbol	MIN.	TYP.	MAX.	Unit	Test Conditions
Zero Gate Voltage Drain Current	I _{DSS}			-1	μΑ	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$
Gate Leakage Current	I _{GSS}			∓100	nA	$V_{GS} = \mp 20 \text{ V}, V_{DS} = 0 \text{ V}$
Gate Cut-off Voltage	$V_{GS(off)}$	-1.0		-2.5	V	$V_{DS} = -10 \text{ V}, I_{D} = -1 \text{ mA}$
Forward Transfer Admittance *1	y _{fs}	4.5			S	$V_{DS} = -10 \text{ V}, I_{D} = -5.5 \text{ A}$
Drain to Source On-state	R _{DS(on)1}		9.7	13	mΩ	$V_{GS} = -10 \text{ V}, I_D = -11 \text{ A}$
Resistance *1	R _{DS(on)2}		17	25	mΩ	$V_{GS} = -4.5 \text{ V}, I_D = -11 \text{ A}$
Input Capacitance	C _{iss}		1750		pF	$V_{DS} = -10 \text{ V},$
Output Capacitance	Coss		850		pF	$V_{GS} = 0 V$,
Reverse Transfer Capacitance	C _{rss}		770		pF	f = 1 MHz
Turn-on Delay Time	t _{d(on)}		20		ns	$V_{DD} = -15 \text{ V}, I_D = -5.5 \text{ A},$
Rise Time	t _r		32		ns	$V_{GS} = -10 \text{ V},$
Turn-off Delay Time	$t_{d(off)}$		70		ns	$R_G = 10 \Omega$
Fall Time	t _f		55		ns	
Total Gate Charge	Q_{G}		45		nC	$V_{DD} = -24 \text{ V},$
Gate to Source Charge	Q _{GS}		2.5		nC	$V_{GS} = -10 \text{ V},$
Gate to Drain Charge	Q_{GD}		23		nC	$I_D = -11 \text{ A}$
Body Diode Forward Voltage *1	$V_{F(S-D)}$		0.85		V	I _F = 11 A, V _{GS} = 0 V
Reverse Recovery Time	t _{rr}		49		ns	$I_F = 11 \text{ A}, V_{GS} = 0 \text{ V},$
Reverse Recovery Charge	Q _{rr}		48		nC	di/dt = 100 A/μs

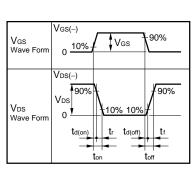
Note: *1. Pulsed

TEST CIRCUIT 1 AVALANCHE CAPABILITY



TEST CIRCUIT 2 SWITCHING TIME





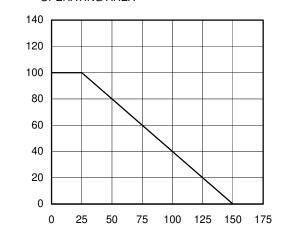
TEST CIRCUIT 3 GATE CHARGE

$$\begin{array}{c|c} D.U.T. \\ \hline \\ IG = -2 \text{ mA} \\ \hline \\ PG. \\ \hline \\ \end{array}$$

dT - Percentage of Rated Power - %

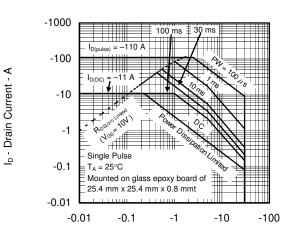
TYPICAL CHARACTERISTICS (T_A = 25°C)

DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



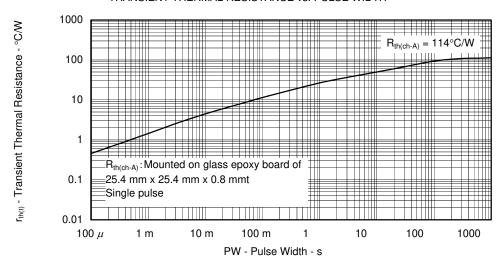
T_A - Ambient Temperature - °C

FORWARD BIAS SAFE OPERATING AREA



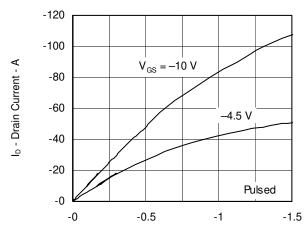
V_{DS} - Drain to Source Voltage - V

TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



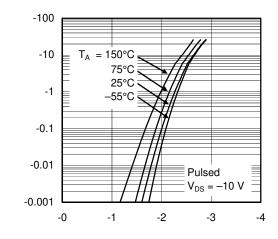
Ip - Drain Current - A

DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



 V_{DS} - Drain to Source Voltage - V

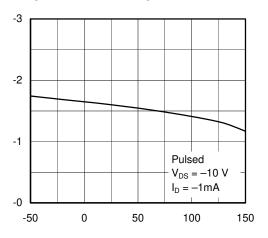
FORWARD TRANSFER CHARACTERISTICS



V_{GS} - Gate to Source Voltage - V

V_{GS(off)} - Gate to Source Cut-off Voltage - V

GATE TO SOURCE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE

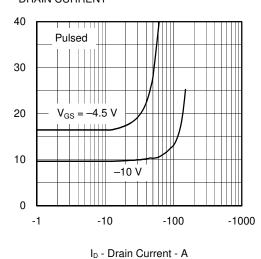


T_{ch} - Channel Temperature - °C

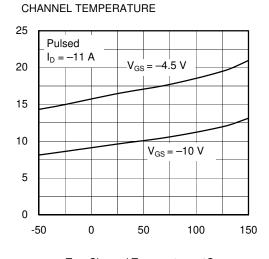
 $R_{\text{DS(on)}}$ - Drain to Source On-state Resistance - $m\Omega$

 $R_{\text{DS(on)}}$ - Drain to Source On-state Resistance - $m\Omega$

DRAIN TO SOURCE ON-STATE RESISTANCE vs. **DRAIN CURRENT**

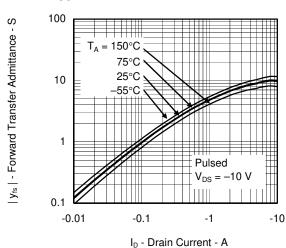


DRAIN TO SOURCE ON-STATE RESISTANCE vs.

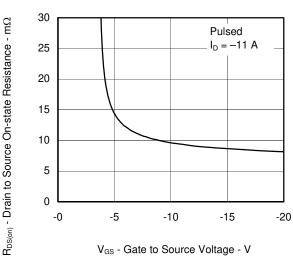


 T_{ch} - Channel Temperature - $^{\circ}C$

FORWARD TRANSFER ADMITTANCE vs. DRAIN **CURRENT**

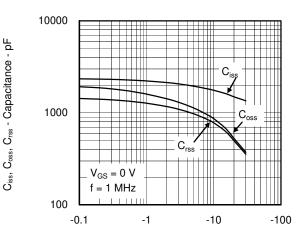


DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



V_{GS} - Gate to Source Voltage - V

CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE

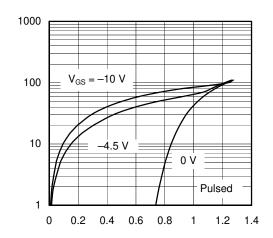


 V_{DS} - Drain to Source Voltage - V

DYNAMIC INPUT/OUTPUT CHARACTERISTICS

-25 V_{DS} - Drain to Source Voltage - V -20 -8 $V_{\text{GS}} \\$ -15 -6 -10 -4 -5 -2 $I_{D} = -11 A$ -0 -0 0 10 20 30 40 50 $\ensuremath{\mathsf{Q}}_{\ensuremath{\mathsf{G}}}$ - Gate Charge - nC

SOURCE TO DRAIN DIODE FORWARD VOLTAGE



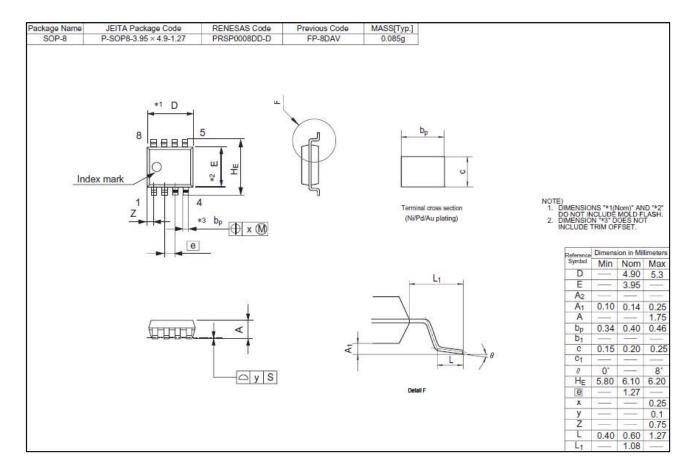
 $V_{\text{F(S-D)}}$ - Source to Drain Voltage - V

V_{GS} - Gate to Source Voltage - V

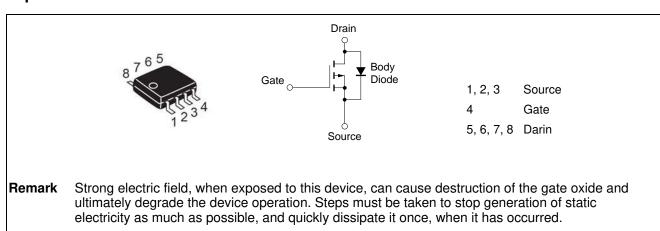
I_F - Diode Forward Current - A

Package Drawings (Unit: mm)

SOP-8



Equivalent Circuit



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